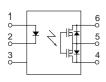
<u>VUT</u> 🕑 LR



GU (General Use) Type SOP Series [1-Channel (Form B) Type]



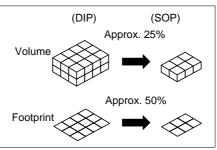
mm inch



FEATURES

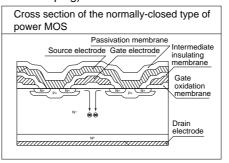
1.1 channel (Form B) in super miniature design

The device comes in a super-miniature SO package measuring (W) $4.4 \times (L) 6.3 \times (H) 2.1 \text{ mm} (W) .173 \times (L) .248 \times (H) .083$ inch —approx. 25% of the volume and 50% of the footprint size of DIP type PhotoMOS Relays.



2. Low on resistance (Max. 50 Ω) at 400 V for normally-closed type has been achieved thanks to the built-in MOSFET processed by our proprietary method, DSD (Double-Diffused and Se-

lective Doping) method.



PhotoMOS RELAYS

3. Tape and reel

The device comes standard in a tape and reel (1,000 pcs./reel) to facilitate automatic insertion machines.

4. Controls low-level analog signals PhotoMOS relays feature extremely low closed-circuit offset voltage to enable control of low-level analog signals without distortion.

5. Low-level off state leakage current In contrast to the SSR with an off state leakage current of several milliamps, the PhotoMOS relay features a very small off state leakage current of only 100 pA even at the rated load voltage of 400 V.

6. Low thermal electromotive force (Approx. 1 $\mu\text{V})$

TYPICAL APPLICATIONS

- Telephones
- Measuring instruments
- Computer
- Industrial robots
- High-speed inspection machines

TYPES

Туре	Output ratings*		Part	Packing quantity in	
	Load voltage	Load current	Picked from the 1/2/3-pin side	Picked from the 4/5/6-pin side	tape and reel
AC/DC	400 V	100 mA	AQV414SX	AQV414SZ	1,000 pcs.

*Indicate the peak AC and DC values.

- Notes: (1) Tape package is the standard packing style. Also available in tube. (Part No. suffix "X" ro "Z" is not needed when ordering; Tube: 75 pcs.; Case: 1,500 pcs.)
 - (2) For space reasons, the top two letters of the product number "AQ" are ommitted on the product seal. The package type indicator "X" and "Z" are also omitted from the seal. (Ex. the label for product number AQV414S is V414S).

RATING

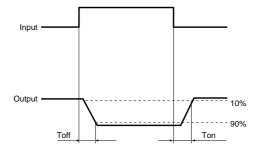
1. Absolute maximum ratings (Ambient temperature: 25°C 77°F)

	Item	Symbol	Type of connection	AQV414S	Remarks	
Input	LED forward current	١F		50 mA		
	LED reverse voltage	Vr		3 V		
	Peak forward current	IFP		1 A	f = 100 Hz, Duty factor = 0.1%	
	Power dissipation	Pin		75 mW		
Output	Load voltage (peak AC)	VL		400 V		
	Continuous load current	IL.	А	0.10 A	A connection: Peak AC, DC B,C connection: DC	
			В	0.11 A		
			С	0.12 A		
	Peak load current	Ipeak		0.3 A	A connection: 100 ms (1 shot) VL= DC	
	Power dissipation	Pout		450 mW		
Total power dissipation		P⊤		500 mW		
I/O isolation voltage		Viso		1,500 V AC		
Temperature limits	Operating	Topr		−40°C to +85°C −40°F to +185°F	Non-condensing at low temperatures	
	Storage	Tstg		-40°C to +100°C -40°F to +212°F		

	Item		Symbol	Type of connec- tion	AQV414S	Remarks
	LED operate current	Typical	- IFon		0.6 mA	I∟= Max.
Input		Maximum			3 mA	
	LED turn off current	Minimum	Foff		0.4 mA	IL= Max.
		Typical			0.55 mA	
		Typical	VF		1.14 V (1.25 V at I⊧ = 50 mA)	I⊧= 5 mA
	LED dropout voltage	Maximum			1.5 V	
Output	On resistance	Typical	n Ron		26 Ω	I⊧= 5 mA I∟= Max. Within 1 s on time
		Maximum		A	50 Ω	
		Typical	Ron		20 Ω	$I_{F} = 5 \text{ mA}$ $I_{L} = Max.$ Within 1 s on time
		Maximum		В	25 Ω	
		Typical	Ron		10 Ω	I⊧ = 5 mA I∟ = Max. Within 1 s on time
		Maximum		С	12.5 Ω	
	Off state leakage current	Maximum	Leak	—	1 μΑ	IF = 0 V∟ = Max.
Transfer characteristics	Turn on times*	Typical	Ton		0.47 ms	I⊧= 5 mA V∟ = Max.
	Turn on time*	Maximum			1.0 ms	
	Turn off time	Typical	Toff		0.28 ms	I⊧= 5 mA V∟ = Max.
		Maximum			1.0 ms	
		Typical	n Ciso		0.8 pF	f = 1 МНz Vв = 0
	I/O capacitance	Maximum			1.5 pF	
	Initial I/C isolation resistance	Minimum	Riso	_	1,000 MΩ	500 V DC

Note: Recommendable LED forward current I_F = 5mA.

*Turn on/Turn off time



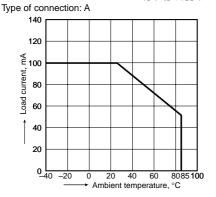
For type of connection, see page 32.

■ For Dimensions, see Page 28. ■ For Schematic and Wiring Diagrams, see Page 32. ■ For Cautions for Use, see Page 36.

REFERENCE DATA

1. Load current vs. ambient temperature characteristics

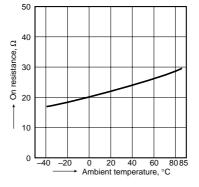
Allowable ambient temperature: -40°C to +85°C -40°F to +185°F



2. On resistance vs. ambient temperature characteristics

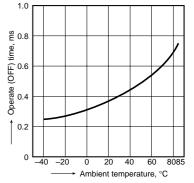
Measured portion: between terminals 4 and 6; LED current: 0 mA;

Continuous load current: 100 mA (DC)



3. Operate (OFF) time vs. ambient temperature characteristics

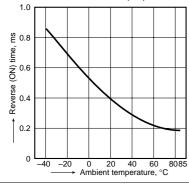
LED current: 5 mA; Load voltage: 400 V (DC); Continuous load current: 100 mA (DC)



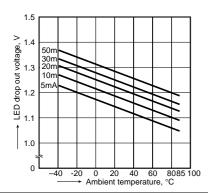
AQV414S

4. Reverse (ON) time vs. ambient temperature characteristics

LED current: 50 mA; Load voltage: 400 V (DC); Continuous load current: 100 mA (DC)

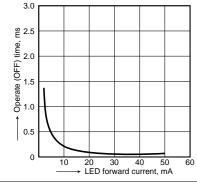


7. LED dropout voltage vs. ambient temperature characteristics LED current: 5 to 50 mA



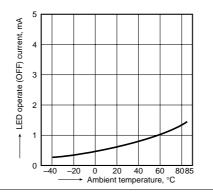
10. LED forward current vs. operate (OFF) time characteristics

Measured portion: between terminals 4 and 6; Load voltage: 400 V (DC); Continuous load current: 100 mA (DC); Ambient temperature: 25°C 77°F



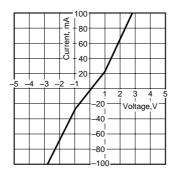
5. LED operate (OFF) current vs. ambient temperature characteristics

. Load voltage: 400 V (DC); Continuous load current: 100 mA (DC)



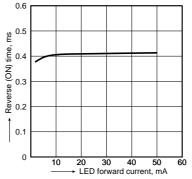
8. Voltage vs. current characteristics of output at MOS portion Measured portion: between terminals 4 and 6;

Ambient temperature: 25°C 77°F

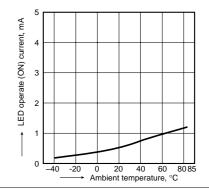


11. LED forward current vs. reverse (ON) time characteristics

Measured portion: between terminals 4 and 6; Load voltage: 400 V (DC); Continuous load current: 100 mA (DC); Ambient temperature: 25°C 77°F

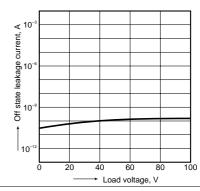


6. LED reverse (ON) current vs. ambient temperature characteristics . Load voltage: 400 V (DC); Continuous load current: 100 mA (DC)



9. Off state leakage current Measured portion: between terminals 4 and 6; LED current: 5 mA;

Ambient temperature: 25°C 77°F



12. Applied voltage vs. output capacitance characteristics

Measured portion: between terminals 4 and 6; Frequency: 1 MHz;

Ambient temperature: 25°C 77°F

